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forming a gate electrode on a substrate;  
forming a gate insulating film on the gate electrode;  
forming a laminate comprising a precursor film for an active layer, and a protective insulating film on the gate insulating film, the protective insulating film having a thickness of 100 nm or less;  
implanting a dopant in one of an LDD region and a source-drain region of the precursor film for the active layer through the protective insulating film without etching; and  
activating the implanted dopant so that a non-doped portion comprises the active layer.

5. (Amended) The method of making a bottom-gate thin-film transistor according to Claim 4, wherein the active layer comprises a polysilicon film.

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6. (Amended) The method of making a bottom-gate thin-film transistor according to Claim 5, wherein, in the laminate forming step, an amorphous silicon film is formed on the gate insulating film, the amorphous silicon film is crystallized to form the polysilicon film, and the protective insulating film is formed on the polysilicon film.

7. (Amended) The method of making a bottom-gate thin-film transistor according to Claim 5, wherein, in the laminate forming step, an amorphous silicon film is formed on the gate insulating film, the protective insulating film is continuously formed on the amorphous silicon film, and then the amorphous silicon film is crystallized to form the polysilicon film.

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8. (Amended) The method of making a bottom-gate thin-film transistor according to Claim 5, wherein, in the laminate forming step, an amorphous silicon film is formed on the gate insulating film, the protective insulating film is formed on a surface of the amorphous silicon film by surface oxidation of the

amorphous silicon film, and then the amorphous silicon film is crystallized to form the polysilicon film.

9. (Amended) A method of making a bottom-gate thin-film transistor according to Claim 4, wherein, subsequent to the dopant implanting step, defects formed in the protective insulating film are recovered.

11. (Amended) A method of fabricating a liquid crystal display device comprising:  
making a bottom-gate thin-film transistor by a method according to any one of Claims 4 to 9;  
forming an interlayer insulating film, a transparent electrode, and an alignment layer on a protective insulating film of the bottom-gate thin-film transistor to comprise a TFT substrate; and  
interposing a liquid crystal between the TFT substrate and a counter substrate provided with a counter electrode.

13. (Amended) A method of fabricating an organic EL device comprising:  
making a bottom-gate thin-film transistor by a method according to any one of Claims 4 to 9;  
forming an interlayer insulating film on a protective insulating film of the bottom-gate thin-film transistor; and  
forming an organic EL element driven by the bottom-gate thin-film transistor on the interlayer insulating film.

**Please add the following new Claim 14.**

14. (New) A method of making a bottom-gate thin-film transistor comprising:  
forming a gate electrode on a substrate;  
forming a gate insulating film on the gate electrode;

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forming a laminate comprising a precursor film for an active layer, and a protective insulating film on the gate insulating film, the protective insulating film having a thickness of 100 nm or less;

implanting a dopant in one of an LDD region and a source-drain region of the precursor film for the active layer through the protective insulating film without etching; and

activating the implanted dopant so that a non-doped portion comprises the active layer;

wherein, subsequent to the dopant implanting step, defects formed in the protective insulating film are recovered.

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